

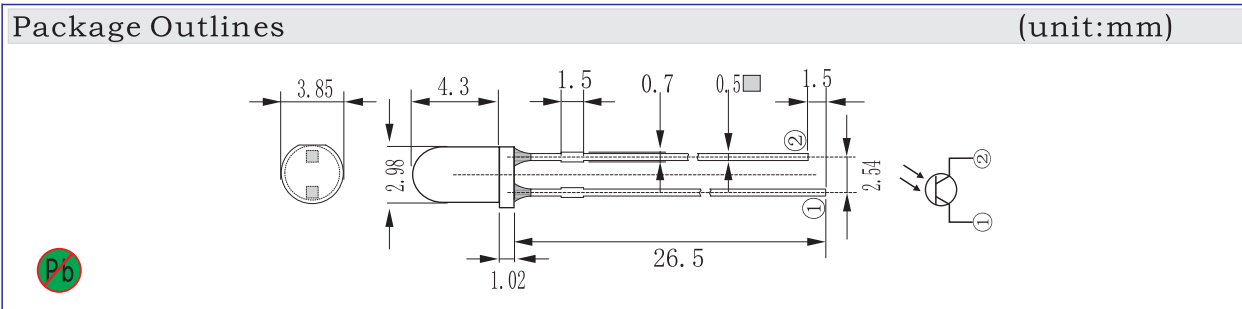


φ3mm Phototransistor T-1

Part Number	Emitting Material	Wave Length λ _D (nm)	Emitting Color	Lens Type	V _F (v)	IV(mcd)	Viewing Angle 2θ _{1/2} (°)
					Typ.	Typ.	
CL-3M4B	GaAlAs	—	—	Black	(at 20 mA)		—

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Collector-Emitter Breakdown Voltage	BV _{CEO}	30	—	100	V	I _C =100μA I _B =0
Emitter-Collector Breakdown Voltage	BV _{ECO}	6.5	—	—	V	I _E =100μA I _B =0
Collector Dark Current	I _{CEO}	—	390	—	nA	V _{CE} =20V H=0mW/cm ²
Collector-Emitter Saturation Voltage	V _{CE(S)}	—	40	—	V	I _C =20mA I _B =100μA
Rise time	T _R	—	15	—	μS	V _{CE} =5V I _C =1mA
Fall time	T _F	—	15	—	μS	RL=1000Ω

Parameter	Symbol	Rating	Unit	Remarks
Forward Current	I _F	30	mA	—
Reverse Voltage	V _R	5	V	—
Operating Temperature	T _{opr}	-25 ~ +85	°C	—
Storage Temperature	T _{Stg}	-40 ~ +100	°C	—
Soldering Temperature	T _{So1}	260	°C	≤3 secretary
Power Dissipation	P _d	75	mW	—



Remark : 1. “△” represents Internal Circuit Feature: A、C、E...Common Cathode, B、D、F...Common Anode.
 2. “□” represents LED Emitted Color.
 3. All dimensions are in millimeters, tolerance is 0.25mm unless otherwise noted.
 4. Above specification is measured by CHANGLI's test instrument and may be changed without notice.
 5. Supplier will reserve authority on material change for above specification.